

Digital Transistors (BRT) R1 = 2.2 k Ω , R2 = 2.2 k Ω

PNP Transistors with Monolithic Bias Resistor Network

MUN2131, MMUN2131L, MUN5131, DTA123EE, DTA123EM3, NSBA123EF3

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

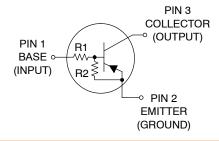
MAXIMUM RATINGS (T_A = 25°C)

| Rating | Symbol | Max | Unit |
|--------------------------------|----------------------|-----|------|
| Collector-Base Voltage | V_{CBO} | 50 | Vdc |
| Collector-Emitter Voltage | V_{CEO} | 50 | Vdc |
| Collector Current – Continuous | Ic | 100 | mAdc |
| Input Forward Voltage | $V_{IN(fwd)}$ | 12 | Vdc |
| Input Reverse Voltage | V _{IN(rev)} | 10 | Vdc |

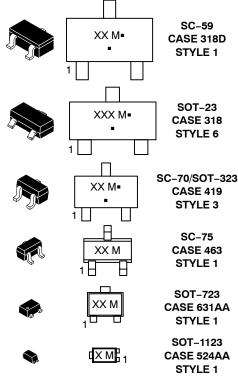
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1

PIN CONNECTIONS



MARKING DIAGRAMS



XXX = Specific Device Code

M = Date Code*
= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}Date Code orientation may vary depending upon manufacturing location.

Table 1. ORDERING INFORMATION

| Device | Part Marking | Package | Shipping [†] |
|--------------------------------|--------------|----------------------------|-----------------------|
| MUN2131T1G | 6H | SC-59 (Pb-Free) | 3000 / Tape & Reel |
| MMUN2131LT1G, NSVMMUN2131LT1G* | A6H | SOT-23 (Pb-Free) | 3000 / Tape & Reel |
| MUN5131T1G, NSVMUN5131T1G* | 6H | SC-70/SOT-323 (Pb-Free) | 3000 / Tape & Reel |
| DTA123EET1G | 6H | SC-75 (Pb-Free) | 3000 / Tape & Reel |
| DTA123EM3T5G, NSVDTA123EM3T5G* | 6H | SOT-723 (Pb-Free) | 8000 / Tape & Reel |
| NSBA123EF3T5G | P (180°)** | SOT-1123 (Pb-Free) | 8000 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{**} (xx°) = Degree rotation in the clockwise direction.

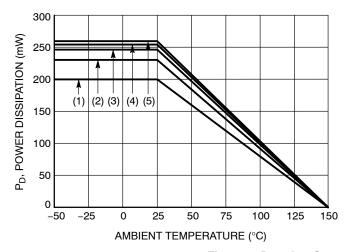


Figure 1. Derating Curve

- (1) SC-75 and SC-70/SOT323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm², 1 oz. copper trace
- (5) SOT-723; Minimum Pad

Table 2. THERMAL CHARACTERISTICS

| Characteristic | | Symbol | Max | Unit |
|---|--|-----------------------------------|--------------------------|-------------|
| THERMAL CHARACTERISTICS (SC-59) (MUN2131) | | | | |
| Total Device Dissipation $T_{A} = 25^{\circ}C$ Derate above 25°C | (Note 1) (Note 2) (Note 1) (Note 2) | P _D | 230 338 1.8 2.7 | mW mW/°C |
| Thermal Resistance, Junction to Ambient | (Note 1) (Note 2) | $R_{	heta JA}$ | 540 370 | °C/W |
| Thermal Characterization Parameter, Junction to Lead Thermal Characterization Parameter, Junction to Top | | $\Psi_{\sf JL} \ \Psi_{\sf JT}$ | 264 287 | °C/W |
| Junction and Storage Temperature Range | | T _J , T _{stg} | -55 to +150 | °C |
| THERMAL CHARACTERISTICS (SOT-23) (MMUN2131L) | | | | |
| Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C | (Note 1) (Note 2) (Note 1) (Note 2) | P _D | 246 400 2.0 3.2 | mW mW/°C |
| Thermal Resistance, Junction to Ambient | (Note 1) (Note 2) | $R_{	hetaJA}$ | 508 311 | °C/W |
| Thermal Characterization Parameter, Junction to Lead Thermal Characterization Parameter, Junction to Top | | $\Psi_{\sf JL} \ \Psi_{\sf JT}$ | 174 208 | °C/W |
| Junction and Storage Temperature Range | | T _J , T _{stg} | -55 to +150 | °C |
| THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5131) | | | | |
| Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C | (Note 1) (Note 2) (Note 1) (Note 2) | P _D | 202 310 1.6 2.5 | mW mW/°C |
| Thermal Resistance, Junction to Ambient | (Note 1) (Note 2) | $R_{	hetaJA}$ | 618 403 | °C/W |
| Thermal Characterization Parameter, Junction to Lead Thermal Characterization Parameter, Junction to Top | | $\Psi_{\sf JL} \ \Psi_{\sf JT}$ | 280 332 | °C/W |
| Junction and Storage Temperature Range | | T_J , T_{stg} | -55 to +150 | °C |
| THERMAL CHARACTERISTICS (SC-75) (DTA123EE) | | | | |
| Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C | (Note 1) (Note 2) (Note 1) (Note 2) | P _D | 200 300 1.6 2.4 | mW mW/°C |
| Thermal Resistance, Junction to Ambient | (Note 1) (Note 2) | $R_{	hetaJA}$ | 600 400 | °C/W |
| Thermal Characterization Parameter, Junction to Lead Thermal Characterization Parameter, Junction to Top | | $\Psi_{\sf JL} \ \Psi_{\sf JT}$ | 277 245 | °C/W |
| Junction and Storage Temperature Range | | T _J , T _{stg} | -55 to +150 | °C |
| THERMAL CHARACTERISTICS (SOT-723) (DTA123EM3) | | | | |
| Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C | (Note 1) (Note 2) (Note 1) (Note 2) | P _D | 260 600 2.0 4.8 | mW mW/°C |

- 1. FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 Inch Pad.
 FR-4 @ 100 mm², 1 oz. copper traces, still air.
 FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 2. THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit | |
|---|--|-----------------------------------|--------------------------|-------------|
| THERMAL CHARACTERISTICS (SOT-723) (DTA123EM3) | • | | | |
| Thermal Resistance, Junction to Ambient | (Note 1) (Note 2) | $R_{	hetaJA}$ | 480 205 | °C/W |
| Junction and Storage Temperature Range | | T _J , T _{stg} | -55 to +150 | °C |
| THERMAL CHARACTERISTICS (SOT-1123) (NSBA123EF3) | <u> </u> | | | |
| Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C | (Note 3) (Note 4) (Note 3) (Note 4) | P _D | 254 297 2.0 2.4 | mW mW/°C |
| Thermal Resistance, Junction to Ambient | (Note 3) (Note 4) | R_{\thetaJA} | 493 421 | °C/W |
| Thermal Characterization Parameter, Junction to Lead Thermal Characterization Parameter, Junction to Top | | $\Psi_{\sf JL} \ \Psi_{\sf JT}$ | 110 85 | °C/W |
| Junction and Storage Temperature Range | | T _J , T _{stg} | -55 to +150 | °C |

^{1.} FR-4 @ Minimum Pad.

Table 3. ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)

| Characteristic | Symbol | Min | Тур | Max | Unit |
|--|--------------------------------|-----|-----|------|------|
| OFF CHARACTERISTICS | | | | | |
| Collector-Base Cutoff Current (V _{CB} = 50 V, I _E = 0) | I _{CBO} | _ | _ | 100 | nAdc |
| Collector-Emitter Cutoff Current (V _{CE} = 50 V, I _B = 0) | I _{CEO} | _ | - | 500 | nAdc |
| Emitter-Base Cutoff Current $(V_{EB} = 6.0 \text{ V, } I_C = 0)$ | I _{EBO} | _ | - | 2.3 | mAdc |
| Collector–Base Breakdown Voltage ($I_C = 10 \mu A, I_E = 0$) | V _{(BR)CBO} | 50 | - | - | Vdc |
| Collector–Emitter Breakdown Voltage (Note 5) $(I_C = 2.0 \text{ mA}, I_B = 0)$ | V _(BR) CEO | 50 | - | - | Vdc |
| ON CHARACTERISTICS | • | • | • | | |
| DC Current Gain (Note 5) ($I_C = 5.0 \text{ mA}$, $V_{CE} = 10 \text{ V}$) | h _{FE} | 8.0 | 15 | - | |
| Collector–Emitter Saturation Voltage (Note 5) ($I_C = 10 \text{ mA}, I_B = 5.0 \text{ mA}$) | V _{CE(sat)} | _ | - | 0.25 | Vdc |
| Input Voltage (off) $(V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A})$ | V _{i(off)} | _ | 1.2 | 0.5 | Vdc |
| Input Voltage (on) (V _{CE} = 0.3 V, I _C = 20 mA) | V _{i(on)} | 2.0 | 1.7 | - | Vdc |
| Output Voltage (on) $(V_{CC} = 5.0 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1.0 \text{ k}\Omega)$ | V _{OL} | _ | - | 0.2 | Vdc |
| Output Voltage (off) ($V_{CC} = 5.0 \text{ V}$, $V_B = 0.25 \text{ V}$, $R_L = 1.0 \text{ k}\Omega$) | V _{OH} | 4.9 | - | - | Vdc |
| Input Resistor | R1 | 1.5 | 2.2 | 2.9 | kΩ |
| Resistor Ratio | R ₁ /R ₂ | 0.8 | 1.0 | 1.2 | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

^{2.} FR-4 @ 1.0 x 1.0 Inch Pad.

FR-4 @ 100 mm², 1 oz. copper traces, still air.
 FR-4 @ 500 mm², 1 oz. copper traces, still air.

TYPICAL CHARACTERISTICS MUN2131, MMUN2131L, MUN5131, DTA123EE, DTA123EM3

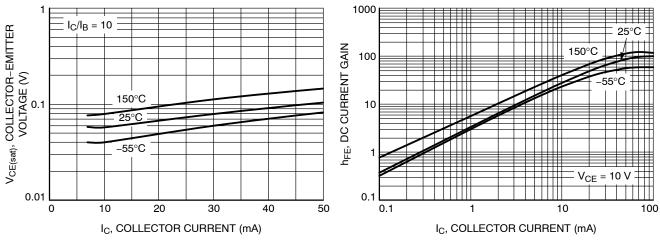


Figure 2. V_{CE(sat)} vs. I_C

Figure 3. DC Current Gain

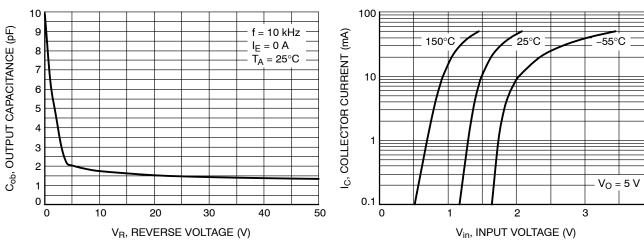


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

4

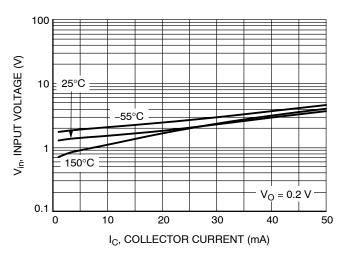


Figure 6. Input Voltage vs. Output Current

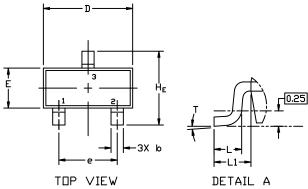




SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023









NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| | MILLIM | ETERS | | | INCHES | |
|-----|--------|-------|------|-------|--------|-------|
| DIM | MIN. | N□M. | MAX. | MIN. | N□M. | MAX. |
| Α | 0.89 | 1.00 | 1.11 | 0.035 | 0.039 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.000 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.017 | 0.020 |
| С | 0.08 | 0.14 | 0.20 | 0.003 | 0.006 | 0.008 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| Ε | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.080 |
| L | 0.30 | 0.43 | 0.55 | 0.012 | 0.017 | 0.022 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.027 |
| HE | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |
| Т | 0* | | 10° | 0* | | 10° |

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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| DESCRIPTION: | SOT-23 (TO-236) | | PAGE 1 OF 2 |

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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

| STYLE 1 THRU 5: CANCELLED | STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR | STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE | N | |
|---|---|---|---|---|---|
| STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE | STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE | STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE | STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE | STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE | STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE |
| STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE | STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE | STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE | STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE | STYLE 19: N PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE | STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE |
| STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN | STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT | STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE | STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE | STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE | STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION |
| STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE | STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE | | | | |

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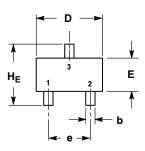
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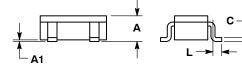




SC-59 CASE 318D-04 ISSUE H

DATE 28 JUN 2012





GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code М

= Pb-Free Package*

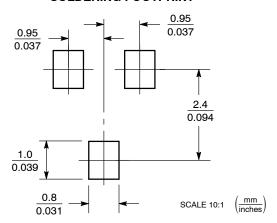
(*Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.

| | М | ILLIMETE | RS | | INCHES | |
|-----|------|----------|------|-------|--------|-------|
| DIM | MIN | NOM | MAX | MIN | MOM | MAX |
| Α | 1.00 | 1.15 | 1.30 | 0.039 | 0.045 | 0.051 |
| A1 | 0.01 | 0.06 | 0.10 | 0.001 | 0.002 | 0.004 |
| b | 0.35 | 0.43 | 0.50 | 0.014 | 0.017 | 0.020 |
| С | 0.09 | 0.14 | 0.18 | 0.003 | 0.005 | 0.007 |
| D | 2.70 | 2.90 | 3.10 | 0.106 | 0.114 | 0.122 |
| E | 1.30 | 1.50 | 1.70 | 0.051 | 0.059 | 0.067 |
| е | 1.70 | 1.90 | 2.10 | 0.067 | 0.075 | 0.083 |
| L | 0.20 | 0.40 | 0.60 | 0.008 | 0.016 | 0.024 |
| HE | 2.50 | 2.80 | 3.00 | 0.099 | 0.110 | 0.118 |

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

| STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE | STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE |
|--|---|--|
| STYLE 4: | STYLE 5: | STYLE 6: |
| PIN 1. CATHODE | PIN 1. CATHODE | PIN 1. ANODE |
| 2. N.C. | 2. CATHODE | 2. CATHODE |
| 3. ANODE | 3. ANODE | 3. ANODE/CATHODE |

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|------------------|-------------|--|-------------|
| DESCRIPTION: | SC-59 | | PAGE 1 OF 1 |

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SC-70 (SOT-323) **CASE 419** ISSUE R

END VIEW

DATE 11 OCT 2022

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

| | MILLIMETERS | | | | INCHES | |
|-----|-------------|------|------|-----------|--------|-------|
| DIM | MIN. | N□M. | MAX. | MIN. | N□M. | MAX. |
| Α | 0.80 | 0.90 | 1.00 | 0.032 | 0.035 | 0.040 |
| A1 | 0.00 | 0.05 | 0.10 | 0.000 | 0.002 | 0.004 |
| A2 | 0.70 REF | | | 0.028 BSC | | C |
| b | 0.30 | 0.35 | 0.40 | 0.012 | 0.014 | 0.016 |
| С | 0.10 | 0.18 | 0.25 | 0.004 | 0.007 | 0.010 |
| D | 1.80 | 2.00 | 2.20 | 0.071 | 0.080 | 0.087 |
| E | 1.15 | 1.24 | 1.35 | 0.045 | 0.049 | 0.053 |
| е | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e1 | 0.65 BSC | | | 0.026 BS | C | |
| L | 0.20 | 0.38 | 0.56 | 0.008 | 0.015 | 0.022 |
| HE | 2.00 | 2.10 | 2.40 | 0.079 | 0.083 | 0.095 |



GENERIC MARKING DIAGRAM

SIDE VIEW



= Specific Device Code XX

М = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

| STYLE 1: CANCELLED | STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE | STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE | STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE | |
|-----------------------------|---|---|--|--|---------------------------|
| STYLE 6: | STYLE 7: | STYLE 8: | STYLE 9: | STYLE 10: | STYLE 11: |
| PIN 1. EMITTER | PIN 1. BASE | PIN 1. GATE | PIN 1. ANODE | PIN 1. CATHODE | PIN 1. CATHODE |
| 2. BASE | 2. EMITTER | 2. SOURCE | 2. CATHODE | 2. ANODE | CATHODE |
| COLLECTOR | COLLECTOR | 3. DRAIN | CATHODE-ANODE | 3. ANODE-CATHODE | CATHODE |

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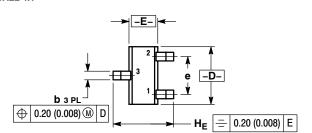
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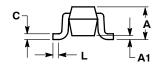




SC-75/SOT-416 **CASE 463 ISSUE G**

DATE 07 AUG 2015





STYLE 1: PIN 1. BASE 2. EMITTER STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. COLLECTOR 3. CATHODE STYLE 4: STYLE 5: PIN 1. CATHODE 2. CATHODE PIN 1. GATE 2. SOURCE

3. DRAIN

GENERIC MARKING DIAGRAM*

3. ANODE



XX = Specific Device Code Μ = Date Code

= Pb-Free Package

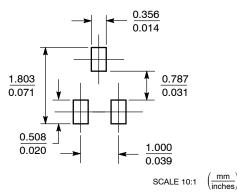
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

NOTES

1. DIMENSIONING AND TOLERANCING PER ANSI Y14,5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

| | MILLIMETERS | | | | INCHES | ; |
|-----|-------------|---------|------|-------|----------|-------|
| DIM | MIN | NOM | MAX | MIN | NOM | MAX |
| Α | 0.70 | 0.80 | 0.90 | 0.027 | 0.031 | 0.035 |
| A1 | 0.00 | 0.05 | 0.10 | 0.000 | 0.002 | 0.004 |
| b | 0.15 | 0.20 | 0.30 | 0.006 | 0.008 | 0.012 |
| С | 0.10 | 0.15 | 0.25 | 0.004 | 0.006 | 0.010 |
| D | 1.55 | 1.60 | 1.65 | 0.061 | 0.063 | 0.065 |
| E | 0.70 | 0.80 | 0.90 | 0.027 | 0.031 | 0.035 |
| е | 1 | .00 BSC |) | C | 0.04 BSC | |
| L | 0.10 | 0.15 | 0.20 | 0.004 | 0.006 | 0.008 |
| HE | 1.50 | 1.60 | 1.70 | 0.060 | 0.063 | 0.067 |

RECOMMENDED **SOLDERING FOOTPRINT***



*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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|------------------|---------------|--|-------------|--|
| DESCRIPTION: | SC-75/SOT-416 | | PAGE 1 OF 1 | |

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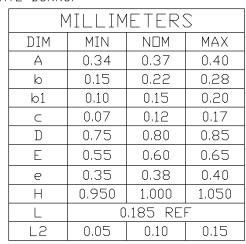


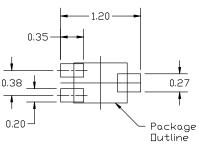
SOT-1123 0.80x0.60x0.37, 0.35P CASE 524AA ISSUE D

DATE 18 JAN 2024

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS
 OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.



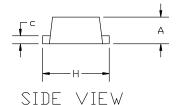


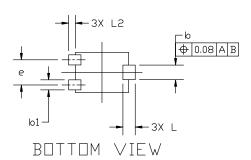
RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download th e □N Semiconductor Soldering and Mounting Techniques Reference manual, S□L□ERRM/□.

| - I | B I |
|-----|--------|
| | E U |

THP VIFW





GENERIC MARKING DIAGRAM*



X = Specific Device Code

M = Date Code

^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

| YLE 1: | STYLE 2: | STYLE 3: | STYLE 4: | STYLE 5: |
|-----------------------------|---------------------------|---------------------------|----------------|--------------------------|
| PIN 1. BASE | PIN 1. ANODE | PIN 1. ANODE | PIN 1. CATHODE | PIN 1. GATE |
| EMITTER | 2. N/C | 2. ANODE | 2. CATHODE | SOURCE |
| COLLECTOR | CATHODE | CATHODE | 3. ANODE | 3. DRAIN |

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| DESCRIPTION: | SOT-1123 0.80x0.60x0.37, | 0.35P | PAGE 1 OF 1 | |

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MILLIMETERS

 $N\square M$.

0.50



SOT-723 1.20x0.80x0.50, 0.40P CASE 631AA ISSUE E

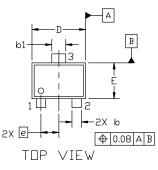
DATE 24 JAN 2024

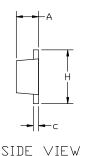
MAX.

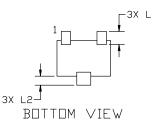
0.55

NOTES:

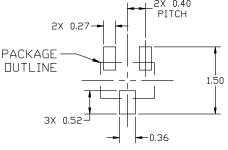
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.







| b | 0.15 | 0.21 | 0.27 | |
|------------------|----------|----------|------|--|
| b1 | 0.25 | 0.31 | 0.37 | |
| С | 0.07 | 0.12 | 0.17 | |
| D | 1.15 | 1.20 | 1.25 | |
| Е | 0.75 | 0.80 | 0.85 | |
| е | 0.40 BSC | | | |
| Н | 1.15 | 1.20 | 1.25 | |
| L | | 0.29 REF | - | |
| L2 | 0.15 | 0.20 | 0.25 | |
| 2X 0.40 PITCH | | | | |



DIM

Α

MIN.

0.45

RECOMMENDED MOUNTING FUUTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

GENERIC MARKING DIAGRAM*



XX = Specific Device Code = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

| STYLE 1: | STYLE 2: | STYLE 3: | STYLE 4: | STYLE 5: |
|-----------------------------|---------------------------|---------------------------|-------------------------|--------------------------|
| PIN 1. BASE | PIN 1. ANODE | PIN 1. ANODE | PIN 1. CATHODE | PIN 1. GATE |
| EMITTER | 2. N/C | 2. ANODE | 2. CATHODE | SOURCE |
| COLLECTOR | CATHODE | CATHODE | ANODE | DRAIN |

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